



100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

60A

Features

- RDS(ON), VGS@10V, ID@30A<12mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

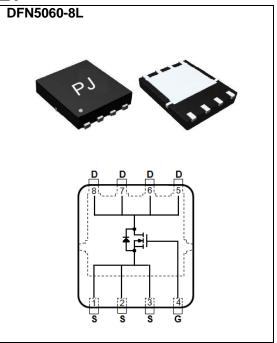
Mechanical Data

• Case: DFN5060-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0028 ounces, 0.08 grams

Marking: Q5478



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	60	A	
	T _C =100°C		38		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	150		
Power Dissipation	T _C =25°C	Po	83	W	
	T _C =100°C		33		
Continuous Drain Current	T _A =25°C	I _D	9	Α	
	T _A =70°C		7.5	Α	
Power Dissipation	T _A =25°C	<u> </u>	2.0	\A/	
	T _A =70°C	Po	1.3	W	
Single Pulse Avalanche Energy ^(Note 6)		E _{AS}	156	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	$R_{ heta JC}$	1.5	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	2	3	4	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =30A	-	9	12	mΩ		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V,V _{GS} =0V	-	-	1.0	uA		
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA		
Dynamic (Note 7)								
Total Gate Charge	Qg	V _{DS} =50V, I _D =30A, V _{GS} =10V ^(Note 1,2)	-	145	-	nC		
Gate-Source Charge	Q _{gs}		-	25	-			
Gate-Drain Charge	Q _{gd}		-	43	-			
Input Capacitance	Ciss	V _{DS} =30V, V _{GS} =0V,	-	3921	-	pF		
Output Capacitance	Coss		-	255	-			
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	96	-			
Turn-On Delay Time	td _(on)		-	27	-	ns		
Turn-On Rise Time	t _r	V_{DD} =50V, I_{D} =30A, V_{GS} =10V, R_{G} =3 Ω (Note 1,2)	-	13	-			
Turn-Off Delay Time	td _(off)		-	15	-			
Turn-Off Fall Time	t _f	$R_{G}=3\Omega$	-	43	-			
Drain-Source Diode								
Maximum Continuous Drain-Source	l _a		-	-	60	А		
Diode Forward Current	I _S							
Diode Forward Voltage	V _{SD}	I _S =30A,V _{GS} =0V	-	0.8	1.3	V		

NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_J (MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.5mH, I_{AS} =25A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

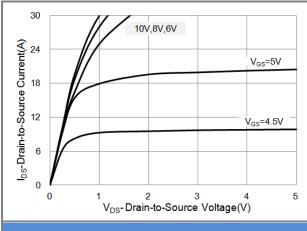


Fig.1 Output Characteristics

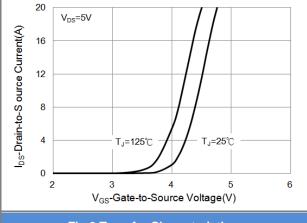


Fig.2 Transfer Characteristics

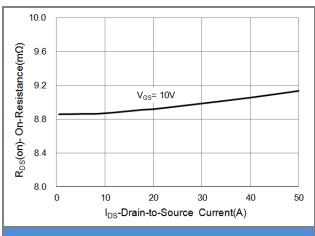


Fig.3 On-Resistance vs. Drain Current

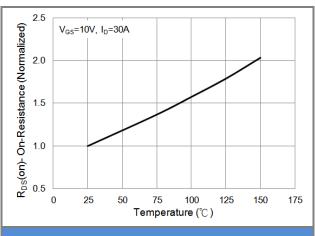
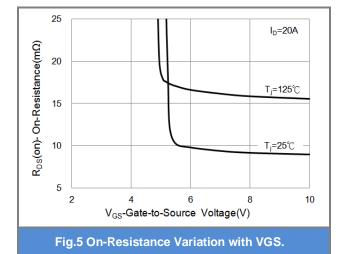


Fig.4 On-Resistance vs. Junction temperature



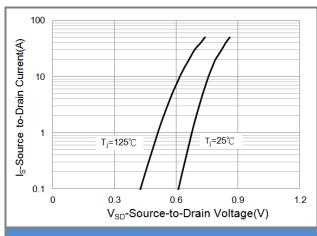


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

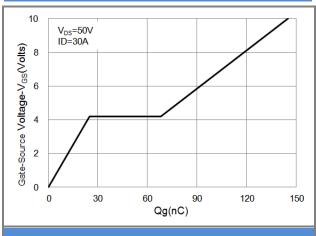


Fig.7 Gate-Charge Characteristics

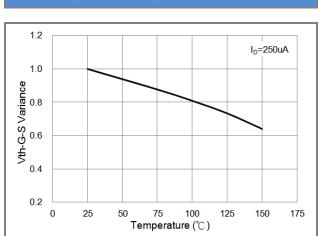
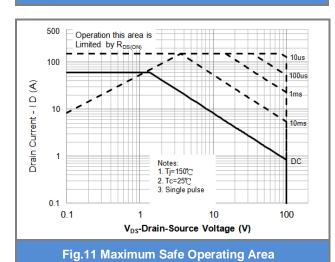


Fig.9 Threshold Voltage Variation with Temperature



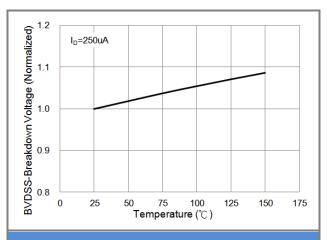


Fig.8 Breakdown Voltage Variation vs. Temperature

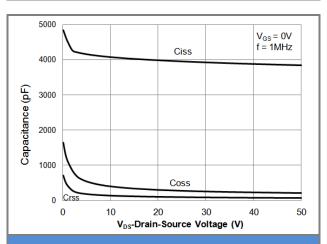


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

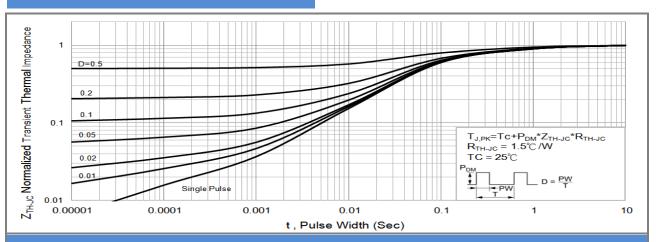


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

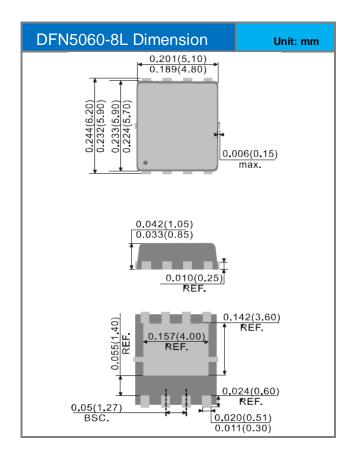


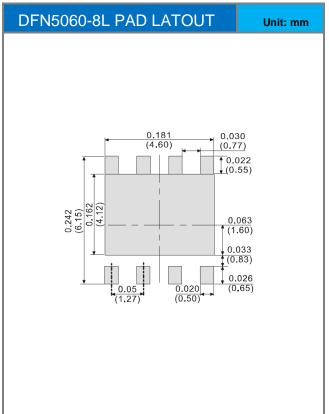


PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version	
PJQ5478_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5478	Halogen free	

Packaging Information & Mounting Pad Layout





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